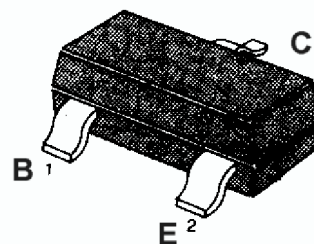


APPLICATION:High Frequency Low Noise Amplifier Application.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CE0}	20	V
Emitter-base voltage	V _{EB0}	4	V
Collector current	I _c	25	mA
Collector Power Dissipation	P _c	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23



1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	28		198		V _{CE} = 5 V, I _c =1mA
Collector Cut-off Current	I _{CB0}			0.1	μA	V _{CB} = 30 V, I _E =0
Emitter Cut-off Current	I _{EB0}			0.1	μA	V _{EB} = 3 V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	30			V	I _c = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	20			V	I _c = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EB0}	4			V	I _E = 0.1mA, I _c =0
Base-Emitter Voltage	V _{BE}		0.72		V	V _{CE} = 5V, I _c =1 mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.3	V	I _c = 10mA, I _B = 1 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			1	V	I _c = 10mA, I _B = 1 mA
Gain bandwidth product	f _T	400			MHz	I _c =1 mA, V _{CE} = 5V
Common Base Output Capacitance	C _{ob}		1.2	1.6	PF	V _{CB} = 10V, I _E =0, f = 1 MHz
Noise Figure	N _F		3	5	dB	V _{CE} = 5 V, I _c = 1mA, f=100 MHz, R _g = 50Ω

h_{FE} Classification And Marking

Print Mark					
Classification	F	G	H	I	
h _{FE}	54~80	72~108	97~146	132~198	